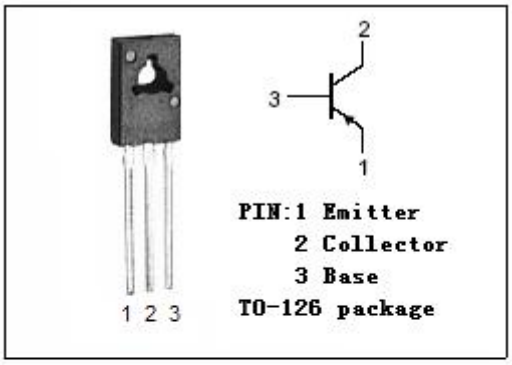
isc Silicon PNP Power Transistor — 2SB1217

DESCRIPTION

- High Collector Current -I_C= -3A
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -60V(Min)
- Good Linearity of h_{FE}
- Low Saturation Voltage
- Complement to Type 2SD1818
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

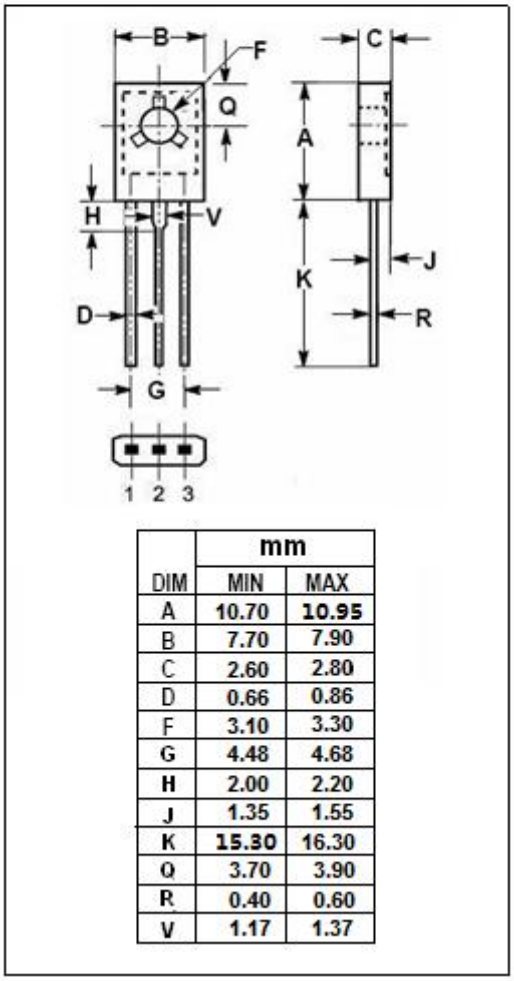


APPLICATIONS

- Designed for use in DC-DC converter, driver, solenid and motor .

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-3	A
I_{CP}	Collector Current-Pulse	-5	A
I_B	Base Current-Continuous	-0.5	A
P_C	Collector Power Dissipation @ T_C=25℃	10	W
	Collector Power Dissipation @ T_a=25℃	1.3	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1.5A; I_B= -0.15A			-0.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -1.5A; I_B= -0.15A			-1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V; I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -7V; I_C= 0			-10	μA
h_{FE-1}	DC Current Gain	I_C= -0.2A ; V_{CE}= -2V	60			
h_{FE-2}	DC Current Gain	I_C= -0.6A ; V_{CE}= -2V	100		400	
h_{FE-3}	DC Current Gain	I_C= -2.0A ; V_{CE}= -2V	50			

◆ **h_{FE-2} Classifications**

M	L	K
100-200	160-320	200-400